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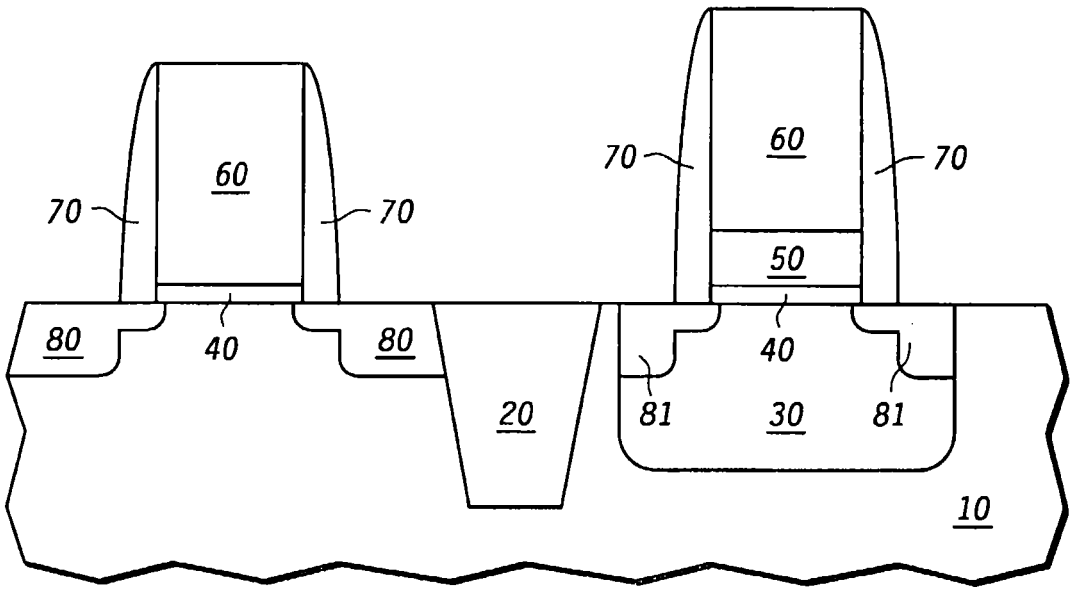
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(54) Title: SEMICONDUCTOR DEVICE AND A METHOD THEREFOR



(57) Abstract: A semiconductor device with dual gate electrodes (60, 50) and its method of formation is taught. A first metal/silicon gate stack and a first gate dielectric (40) are formed over a first doped region. The metal/gate stack (60, 50) comprises a metal portion (50) over the first gate dielectric (40) and a first gate portion (60) over the metal portion (50). A silicon gate (60) and a second gate dielectric (40) are formed over the second doped region. In one embodiment, the first and second gate portions are P+ doped silicon germanium and the metal portion is TaSiN. In another embodiment, the first and second gate portions are N+ doped polysilicon and the metal portion is TaSiN. FIG. 5 accompanies the abstract.

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